



74AUP1G00

SINGLE 2 INPUT POSITIVE NAND GATE

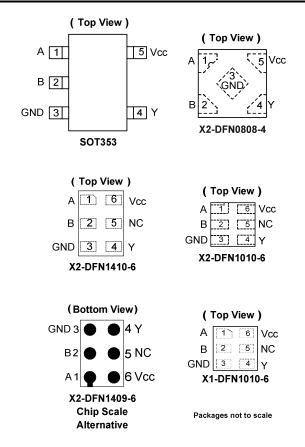
Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP1G00 is a single two-input positive NAND gate with a standard push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

 $Y = \overline{A \bullet B} \ \, \text{or} \ \ \, Y = \overline{A} + \overline{B}$

Pin Assignments



Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4 mA Output Drive at 3.0V
- Low Static Power Consumption I_{CC} < 0.9μA
- Low Dynamic Power Consumption C_{PD} = 6pF (Typical at 3.6V)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at V_{CC} = 3.0V.
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 2000-V Human Body Model (A114)
 Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

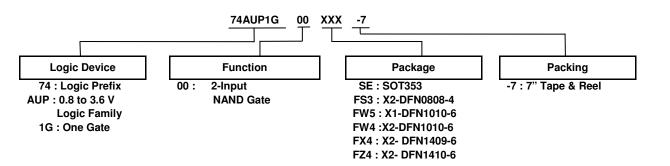
- Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players ,Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G00SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G00FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G00FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

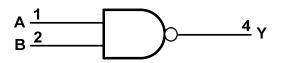
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Function
A	Data Input
В	Data Input
GND	Ground
Y	Data Output
V _{CC}	Supply Voltage

Logic Diagram



Function Table

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI < 0	50	mA
I _{OK}	Output Clamp Current (V _O < 0)	50	mA
lo	Continuous Output Current ($V_O = 0$ to V_{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8) (@T_A = +25 °C, unless otherwise specified.)

Symbol	P	arameter	Min	Мах	Unit
Vcc	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 0.8V$	—	-20	μΑ
		V _{CC} = 1.1V	—	-1.1	
	Llink Louis Output Output	$V_{CC} = 1.4V$	—	-1.7	
I _{ОН}	High-Level Output Current	V _{CC} = 1.65V	—	-1.9	mA
		V _{CC} = 2.3V	—	-3.1	
		V _{CC} = 3.0V	—	-4	
		$V_{CC} = 0.8V$	—	20	μΑ
		V _{CC} = 1.1V	_	1.1	
		$V_{CC} = 1.4V$	_	1.7	
IOL	Low-Level Output Current	V _{CC} = 1.65V	—	1.9	mA
		$V_{CC} = 2.3V$	_	3.1	
		V _{CC} = 3.0V	—	4	1
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 0.8V$ to 3.6V	—	200	ns/V
TA	Operating Free-Air Temperature	•	-40	125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	T _A = -	+25℃	T _A = -40 °C	C to +85℃	Unit
Symbol	Parameter	Test Conditions	VCC	Min	Max	Min	Max	Unit
		—	0.8V to 1.65V	0.80 x V _{CC}	—	0.80 x V _{CC}	—	
Maria	High-Level Input	_	1.65V to 1.95V	0.65 x V _{CC}	—	0.65 x V _{CC}	—	v
VIH	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	v
		—	3.0V to 3.6V	2.0	—	2.0	—	
		—	0.8V to 1.65V	—	0.30 x V _{CC}	—	0.30 x V _{CC}	
VIL	Low-Level Input	—	1.65V to 1.95V	—	$0.35 \times V_{CC}$	—	$0.35 \times V_{CC}$	v
VIL	Voltage	_	2.3V to 2.7V	—	0.7	—	0.7	v
		—	3.0V to 3.6V	—	0.9	—	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	$V_{CC} - 0.1$	—	$V_{CC} - 0.1$	—	
		I _{OH} = -1.1mA	1.1V	0.75 x V _{CC}	—	0.7 x V _{CC}	—	
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—	
.,	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	—	1.3	—	
V _{OH}	Voltage	I _{OH} = -2.3mA	0.01/	2.05	—	1.97	—	V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
		I _{OH} = -2.7mA	a)/	2.72	_	2.67	_	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μΑ	0.8V to 3.6V	—	0.1		0.1	
		$I_{OL} = 1.1 \text{mA}$	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.31		0.35	
V _{OL}	Voltage	$I_{OL} = 2.3 \text{mA}$		—	0.31	—	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		$I_{OL} = 2.7 \text{mA}$		_	0.31	_	0.33	
		$I_{OL} = 4mA$	- 3V	_	0.44	_	0.45	
I	Input Current	A or B Input $V_1 = GND$ to 3.6V	0 to 3.6V	_	± 0.1	_	± 0.5	μA
IOFF	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0	_	0.2	_	0.6	μA
ΔI_{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 = 0 \text{V to } 3.6 \text{V}$	0 V to 0.2V	—	0.2	—	0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8 V to 3.6V	_	0.5	_	0.9	μA
Δlcc	Additional Supply Current	One Input at V_{CC} -0.6V Other Inputs at V_{CC} or GND	3.3V	_	40	_	50	μA



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	N	T _A = -40 ℃	to +125℃	Unit
Symbol	Farameter	Test conditions	Vcc	Min	Max	Unit
		—	0.8V to 1.65V	0.80 x V _{CC}	—	
VIH	High-Level Input Voltage	—	1.65V to 1.95V	0.70 x V _{CC}	—	V
VIH			2.3V to 2.7V	1.6	—	v
			3.0V to 3.6V	2.0	—	
			0.8V to 1.65V	—	$0.25 \times V_{CC}$	
VIL	Low-Level Input Voltage	—	1.65V to 1.95V	—	$0.30 \times V_{CC}$	V
۷IL	Low Lovel input voltage		2.3V to 2.7V		0.7	v
		—	3.0V to 3.6V	—	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11	—	
		I _{OH} = -1.1mA	1.1V	$0.6 \times V_{CC}$		
		I _{OH} = -1.7mA	1.4V	0.93	—	
V	V _{OH} High-Level Output Voltage	I _{OH} = -1.9mA	1.65V	1.17	—	v
∨он	High-Level Output Voltage	I _{OH} = -2.3mA	2.3V	1.77	—	v
		I _{OH} = -3.1mA	2.3V	1.67	—	
		I _{OH} = -2.7mA	0)/	2.40	—	
		I _{OH} = -4mA	3V	2.30	—	
		I _{OL} = 20μΑ	0.8V to 3.6V	—	0.11	
		I _{OL} = 1.1mA	1.1V	—	0.33 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	—	0.41	
		I _{OL} = 1.9mA	1.65V	—	0.39	
V _{OL}	Low-Level Output Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V		0.50	
		I _{OL} = 2.7mA		—	0.36	
		I _{OL} = 4mA	3V		0.50	
lı	Input Current	A or B Input, $V_I = GND$ to 3.6V	0 to 3.6V	—	± 0.75	μA
I _{OFF}	Power Down Leakage Current	V_{I} or $V_{O} = 0V$ to 3.6V	0	—	± 3.5	μA
Δloff	Delta Power Down Leakage Current	V_{I} or $V_{O} = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
I _{CC}	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	—	3.0	μA
ΔI _{CC}	Additional Supply Current	Input at V_{CC} -0.6V Other Inputs at V_{CC} or GND	3.3V	—	75	μA



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From Input	TO OUTPUT	N N	T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃		Unit
			V _{cc}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	—	17.5	_	_	_	_	_	
		8 Y	1.2V ± 0.1V	2.5	5.3	11.0	2.1	12.2	2.1	13.5	ns
+	A or D		1.5V ± 0.1V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	
t _{pd}	A or B		1.8V ± 0.15V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	
			2.5V ± 0.2V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	
			3.3V ± 0.3V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	

$C_L = 10 pF$, See Figure 1

Parameter	From Input	то	Vaa	٦	T _A = +25 ℃		T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃		Unit
Farailleter		OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
		0.8V	_	21.0	_	—	_	—	_		
			1.2V ± 0.1V	2.4	6.1	13.0	2.2	14.4	2.2	15.9	- ns
	A or D	v	1.5V ± 0.1V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	
t _{pd}	A or B	ř	1.8V ± 0.15V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	
		-	2.5V ± 0.2V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	
			3.3V ± 0.3V	1.3	2.8	4.3	1.2	4.9	1.2	5.4	

C_L = 15pF, See Figure 1

Parameter	From Input	TO OUTPUT	V		T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃	
Farameter			Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
		0.8V	_	24.5	—	—	_	—	—		
			1.2V ± 0.1V	3.4	6.9	14.8	3.1	16.5	3.1	18.2	
	A or B	v	1.5V ± 0.1V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	
t _{pd}	AUD	ř	1.8V ± 0.15V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	ns
			2.5V ± 0.2V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	
			$3.3V \pm 0.3V$	1.6	3.2	4.9	1.4	5.7	1.4	6.3	

C_L = 30pF, See Figure 1

Parameter	From	TO OUTPUT	Vaa	-	T _A = +25 ℃			T _A = -40 ℃ to +85 ℃		T _A = -40 ℃ to +125 ℃	
Farameter	Input		V _{cc}	Min	Тур	Max	Min	Мах	Min	Max	Unit
			0.8V	_	34.8	_	_	_	—	_	
			1.2V ± 0.1V	4.6	17.5	22.0	4.1	22.6	4.1	24.9	ns
	A or D	v	1.5V ± 0.1V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	
t _{pd}	A or B	Ŷ	1.8V ± 0.15V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	
			2.5V ± 0.2V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.3	2.6	6.5	2.1	7.6	2.1	8.4	



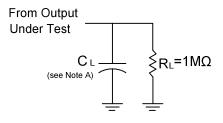
Operating and Package Characteristics (@T_A = +25 °C, unless otherwise specified.)

	Parameter	Test Conditio		V _{cc}	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
0	Power Dissipation	f = 1MH	łz	1.5V ± 0.1V	6.3	~_
C _{pd}	Capacitance	No Loa	ld	1.8V ± 0.15V	6.2	pF
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	$V_i = V_{CC} \text{ or } GND$		0V or 3.3V	1.5	pF
		SOT353		_	371	
		X2-DFN0808-4			430	
0	Thermal Resistance	X1-DFN1010-6			435	
θ_{JA}	Junction-to-Ambient	X2-DFN1010-6	(Note 9)		445	°C/W
		X2-DFN1409-6			470	
		X2-DFN1410-6			460	
		SOT353		_	143	
		X2-DFN0808-4			240	
0	Thermal Resistance	X1-DFN1010-6		_	250	
θJC	Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	°C/W
		X2-DFN1409-6		_	275	1
		X2-DFN1410-6		_	265	1

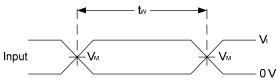
Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



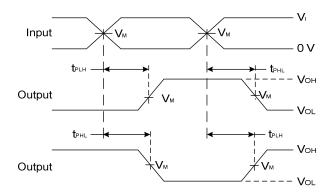
Parameter Measurement Information



Vcc	Inputs		N N	0
VCC	VI	t _r /t _f	V _M	CL
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V±0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

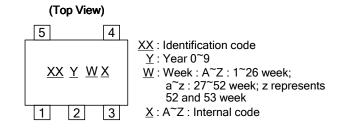
- Notes: A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

 - C. Inputs are measured separately one transition per measurement.
 - D. tPLH and tPHL are the same as tPD.



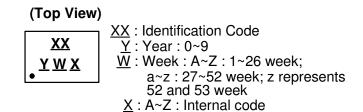
Marking Information

(1) SOT353



Part Number	Package	Identification Code
74AUP1G00SE-7	SOT353	ХН

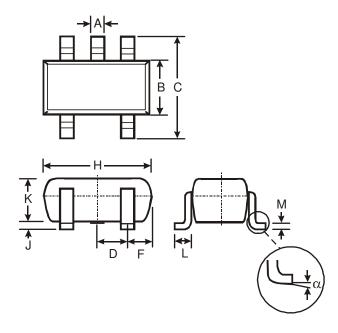
(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6



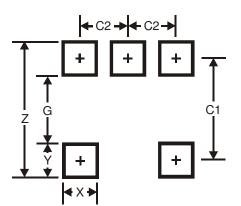
Part Number	Package	Identification Code
74AUP1G00FS3-7	X2-DFN0808-4	YJ
74AUP1G00FW5-7	X1-DFN1010-6	Q1
74AUP1G00FW4-7	X2-DFN1010-6	ХН
74AUP1G00FX4-7	X2-DFN1409-6	HA
74AUP1G00FZ4-7	X2-DFN1410-6	ХН



SOT353 Package Outline Dimensions and Suggested Pad Layout



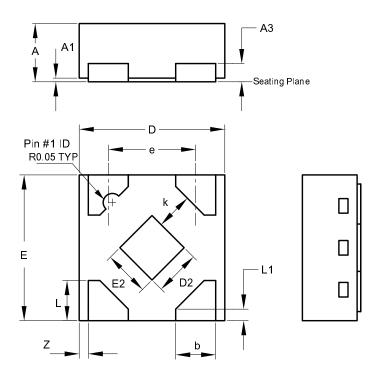
	SOT353					
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D		0.65 Typ)			
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
К	0.90	1.00	1.00			
L	0.25	0.40	0.30			
М	0.10	0.22	0.11			
α	0°	8°	-			
A	All Dimensions in mm					



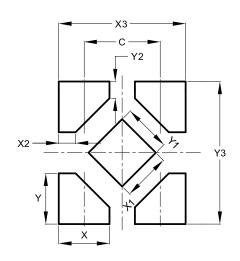
Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
Х	0.42	
Y	0.6	
C1	1.9	
C2	0.65	



X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



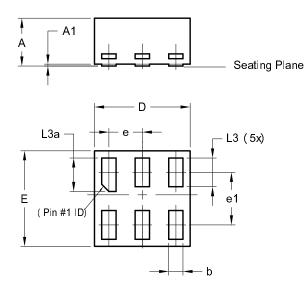
	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
z	-	-	0.05		
A	All Dimensions in mm				



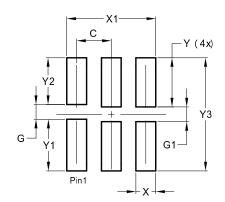
Dimensions	Value
С	0.480
Х	0.320
X1	0.300
X2	0.106
X3	0.800
Y	0.320
Y1	0.300
Y2	0.106
Y3	0.900



X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



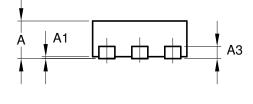
X1-DFN1010-6 (Type B)					
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е		0.35 B	SC		
e1		0.55 B	SC		
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All	All Dimensions in mm				

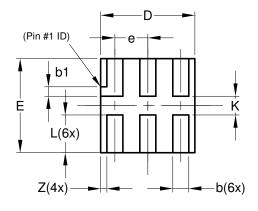


Dimensions	Value
Dimensions	(in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Y	0.500
Y1	0.525
Y2	0.475
Y3	1.150

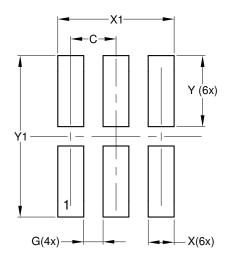


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





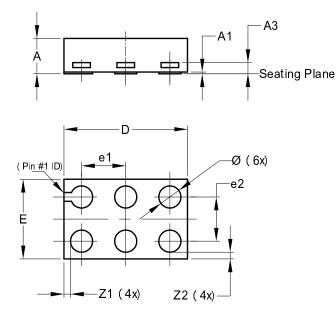
X2-DFN1010-6				
Dim	Min	Мах	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
A3	_		0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_		0.35	
L	0.35	0.45	0.40	
к	0.15			
Z			0.065	
All C	All Dimensions in mm			



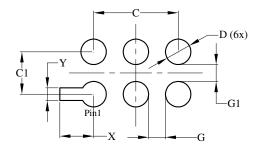
Dimensions	Value (in mm)	
С	0.350	
G	0.150	
X	0.200	
X1	0.900	
Y	0.550	
Y1	1.250	



X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout



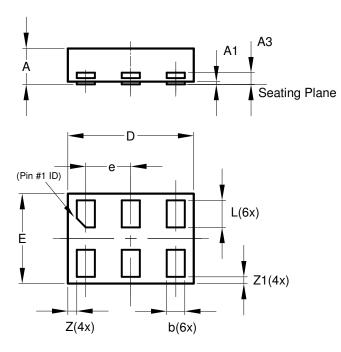
	X2-DFN1409-6				
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
Z1	-	-	0.075		
Z2	-	-	0.075		
All Dimensions in mm					



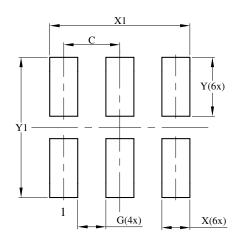
Dimensions	Value (in mm)	
С	1.000	
C1	0.500	
D	0.300	
G	0.200	
G1	0.200	
Х	0.400	
Y	0.150	



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	l	0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е	_	_	0.50	
L	0.25	0.35	0.30	
Z	l		0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
¥1	1.250



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